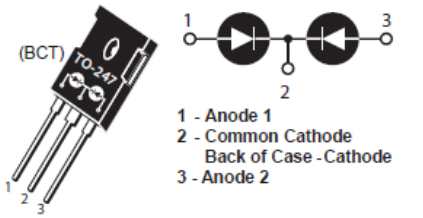
MSC050SDA070BCT Zero Recovery Silicon Carbide Schottky Dual Diode

Product Overview

The silicon carbide (SiC) power Schottky barrier diodes (SBD) product line from Microsemi increases your performance over silicon diode solutions while lowering your total cost of ownership for high-voltage applications. The MSC050SDA070BCT is a 700 V, 50 A SiC dual common cathode SBD in a three-lead TO-247 package shown below.



Features

The following are key features of the MSC050SDA070BCT device:

- No reverse recovery
- Low forward voltage
- Low leakage current
- Avalanche energy rated
- RoHS compliant

Benefits

The following are benefits of the MSC050SDA070BCT device:

- High switching frequency
- Low switching losses
- Low noise (EMI) switching
- Higher reliability systems
- Increased system power density

Applications

The MSC050SDA070BCT device is designed for the following applications:

- Power factor correction (PFC)
- Anti-parallel diode
  - Switch-mode power supply
  - Inverters/converters
  - Motor controllers
- Freewheeling diode
  - Switch-mode power supply
  - Inverters/converters
- Snubber/clamp diode

Electrical Specifications

This section shows the specifications for the MSC050SDA070BCT device. All ratings are per leg.

Absolute Maximum Ratings

The following table shows the absolute maximum ratings for the MSC050SDA070BCT device.

All ratings: T_C = 25 °C unless otherwise specified.

Table 1 • Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
V_R	Maximum DC reverse voltage	700	V
V_{RRM}	Maximum peak repetitive reverse voltage	700	
V_{RWM}	Maximum working peak reverse voltage	700	
I_F	Maximum DC forward current (T_c = 25 °C)	88	A
	Maximum DC forward current (T_c = 135 °C)	39	
	Maximum DC forward current (T_c = 145 °C)	32	
I_{FRM}	Repetitive peak forward surge current (T_c = 25 °C, t_p = 8.3 ms, half sine wave)	128	
I_{FSM}	Non-repetitive forward surge current (T_c = 25 °C, t_p = 8.3 ms, half sine wave)	124	
P_{tot}	Power dissipation (T_c = 25 °C)	283	W
	Power dissipation (T_c = 110 °C)	123	
T_J , T_{STG}	Operating and storage temperature range	–55 to 175	°C
T_L	Lead temperature for 10 seconds	300	
E_{AS}	Single-pulse avalanche energy (starting T_J = 25 °C, L = 0.08 mH, peak I_L = 50 A)	100	mJ

The following table shows the thermal and mechanical characteristics of the MSC050SDA70BCT device.

Table 2 • Thermal and Mechanical Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction-to-case thermal resistance		0.37	0.53	°C/W
W_T	Package weight		0.22		oz

Symbol	Characteristic	Min	Typ	Max	Unit
			5.9		g
	Mounting torque, 6-32 or M3 screw			10	lbf-in
				1.1	N-m

Electrical Performance

The following table shows the static characteristics of the MSC050SDA070BCT device.

Table 3 • Static Characteristics

Symbol	Characteristic	Test Conditions	Typ	Max	Unit
V_F	Forward voltage	I_F = 50 A, T_J = 25 °C	1.5	1.8	V
		I_F = 50 A, T_J = 175 °C	1.9		
I_{RM}	Reverse leakage current	V_R = 700 V, T_J = 25 °C	15	200	µA
		V_R = 700 V, T_J = 175 °C	250		
Q_C	Total capacitive charge	V_R = 400 V, T_J = 25 °C	133		nC
C_J	Junction capacitance	V_R = 1 V, T_J = 25 °C, ƒ = 1 MHz	2034		pF
	Junction capacitance	V_R = 200 V, T_J = 25 °C, ƒ = 1 MHz	248		
	Junction capacitance	V_R = 400 V, T_J = 25 °C, ƒ = 1 MHz	216		

Performance Curves

This section shows the typical performance curves for the MSC050SDA070BCT device.

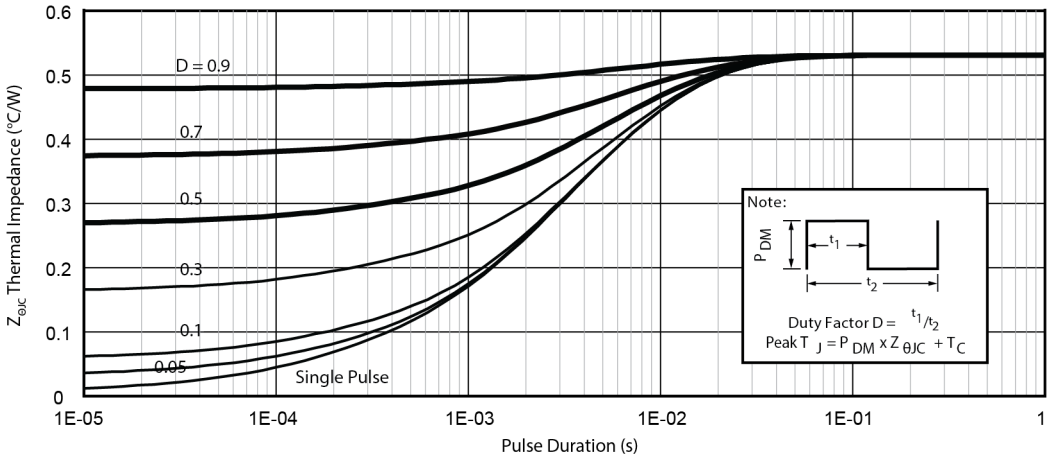


Figure 1 • Maximum Transient Thermal Impedance

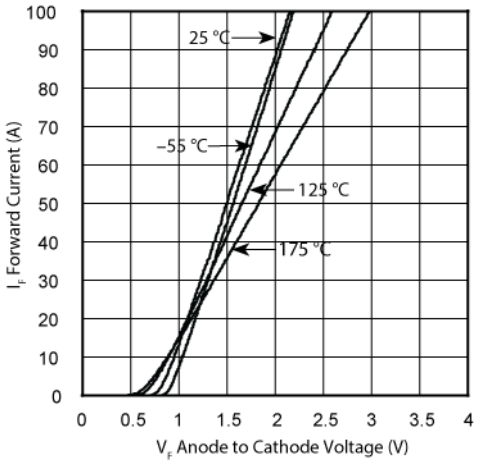


Figure 2 • Forward Current vs Forward Voltage

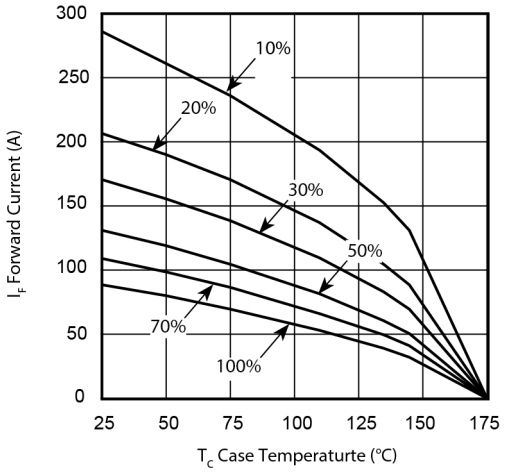


Figure 3 • Max Forward Current vs Case Temp

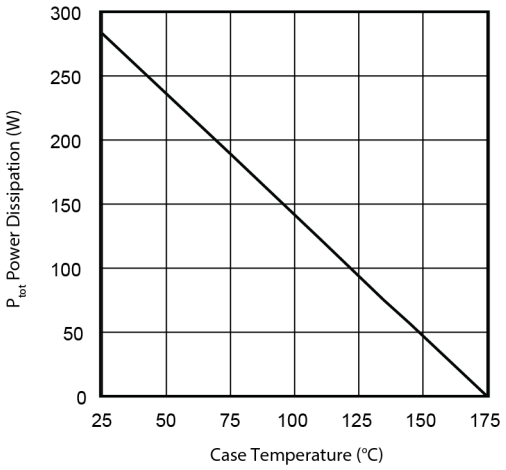


Figure 4 • Max Power Dissipation vs Case Temp

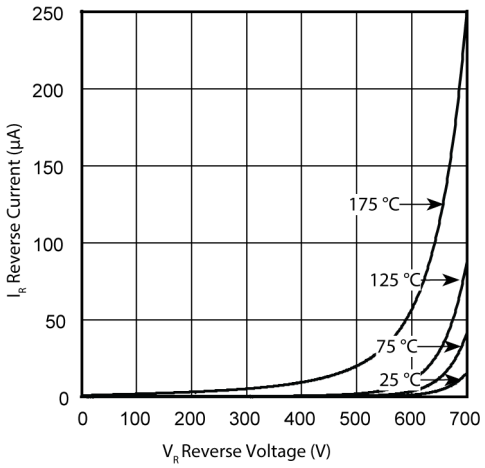


Figure 5 • Reverse Current vs. Reverse Voltage

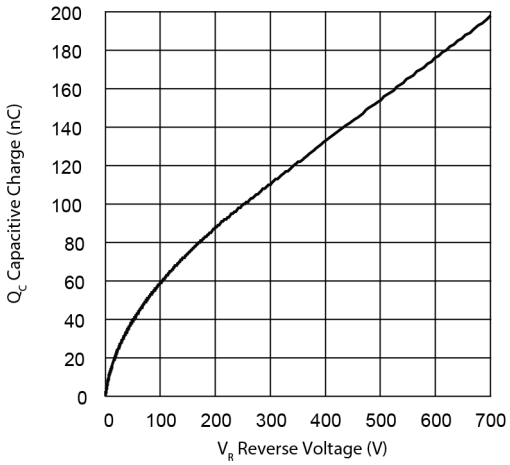


Figure 6 • Total Capacitive Charge vs. V_R

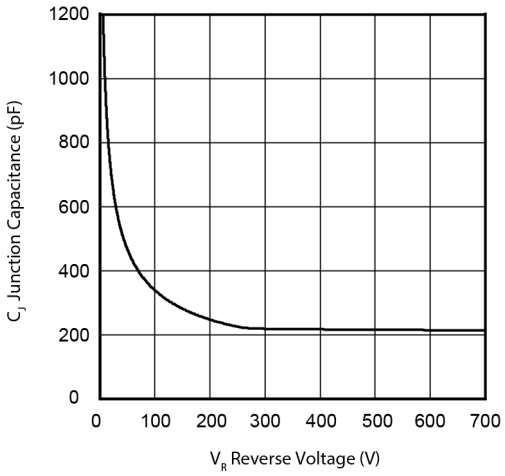


Figure 7 • Junction Capacitance vs V_R

Package Specification

This section outlines the package specification for the MSC050SDA070BCT device.

Package Outline Drawing

This section shows the TO-247 package drawing of the MSC050SDA070BCT device. Dimensions are in millimeters and (inches).

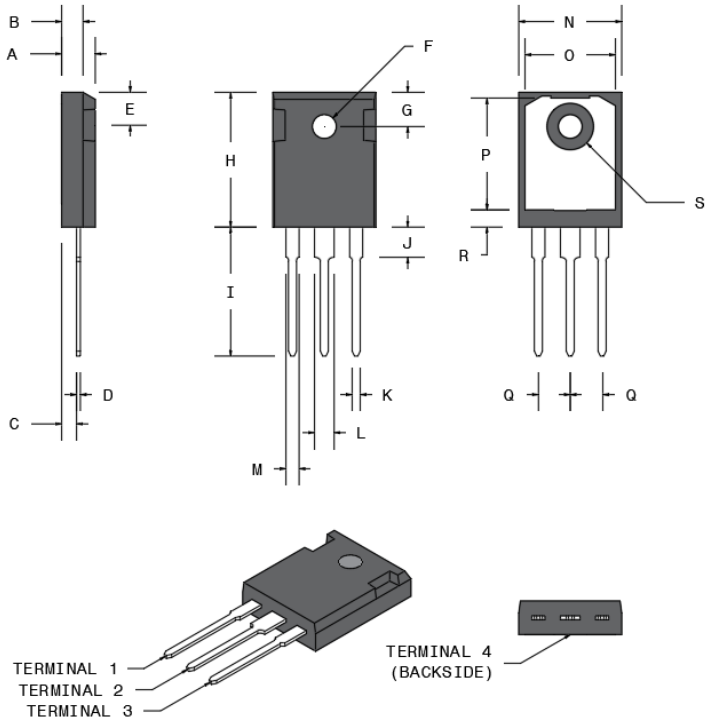


Figure 8 • Package Outline Drawing

The following table shows the TO-247 dimensions and should be used in conjunction with the package outline drawing.

Table 4 • Dimensions

Symbol	Min. (mm)	Max. (mm)	Min. (in.)	Max (in.)
A	4.69	5.31	0.185	0.209
B	1.49	2.49	0.059	0.098
C	2.21	2.59	0.087	0.102
D	0.40	0.79	0.016	0.031
E	5.38	6.20	0.212	0.244
F	3.50	3.81	0.138	0.150

Symbol	Min. (mm)	Max. (mm)	Min. (in.)	Max (in.)
G	6.15 BSC		0.242 BSC	
H	20.80	21.46	0.819	0.845
I	19.81	20.32	0.780	0.800
J	4.00	4.50	0.157	0.177
K	1.01	1.40	0.040	0.055
L	2.87	3.12	0.113	0.123
M	1.65	2.13	0.065	0.084
N	15.49	16.26	0.610	0.640
O	13.50	14.50	0.531	0.571
P	16.50	17.50	0.650	0.689
Q	5.45 BSC		0.215 BSC	
R	2.00	2.75	0.079	0.108
S	7.10	7.50	0.280	0.295
Terminal 1	Anode 1			
Terminal 2	Common cathode			
Terminal 3	Anode 2			
Terminal 4	Common cathode			

Microsemi
2355 W. Chandler Blvd.
Chandler, AZ 85224 USA

Within the USA: +1 (480) 792-7200
Fax: +1 (480) 792-7277

Microsemi Corporation, a subsidiary of Microchip Technology Inc. (Nasdaq: MCHP), and its corporate affiliates are leading providers of smart, connected and secure embedded control solutions. Their easy-to-use development tools and comprehensive product portfolio enable customers to create optimal designs which reduce risk while lowering total system cost and time to market. These solutions serve more than 120,000 customers across the industrial, automotive, consumer, aerospace and defense, communications and computing markets. Headquartered in Chandler, Arizona, the company offers outstanding technical support along with dependable delivery and quality. Learn more at **www.microsemi.com**.

053-4115 | February 2020 | Released

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Microchip:
MSC050SDA070BCT